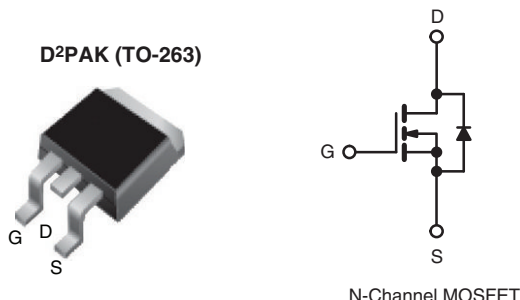


EF Series Power MOSFET with Fast Body Diode

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V	0.098
Q_g (Max.) (nC)	155	
Q_{gs} (nC)	22	
Q_{gd} (nC)	43	
Configuration	Single	



FEATURES

- Fast body diode MOSFET using E series technology
- Reduced t_{rr} , Q_{rr} , and I_{RRM}
- Low figure-of-merit (FOM): $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Telecommunications
 - Server and telecom power supplies
- Lighting
 - High-intensity discharge (HID)
 - Light emitting diodes (LEDs)
- Consumer and computing
 - ATX power supplies
- Industrial
 - Welding
 - Battery chargers
- Renewable energy
 - Solar (PV inverters)
- Switch mode power supplies (SMPS)
 - LLC
 - Phase shifted bridge (ZVS)
 - 3-level inverter
 - AC/DC bridge

ORDERING INFORMATION

Package	D2PAK (TO-263)
Lead (Pb)-free and Halogen-free	SiHB33N60EF-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	A
		$T_C = 100$ °C	
Pulsed Drain Current (Typical) ^a	I_{DM}	100	W/°C
Linear Derating Factor		2.2	
Single Pulse Avalanche Energy ^b	E_{AS}	691	mJ
Maximum Power Dissipation	P_D	278	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C
Drain-Source Voltage Slope	dV/dt	$T_J = 125$ °C	V/ns
Reverse Diode dV/dt ^d			
Soldering Recommendations (Peak Temperature) ^c	for 10 s	300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DS} = 50$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 7$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

**THERMAL RESISTANCE RATINGS**

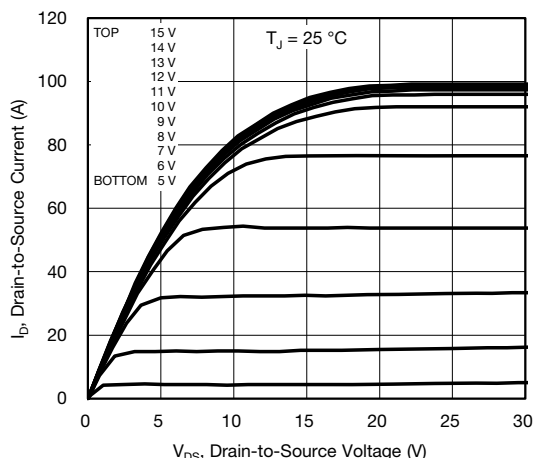
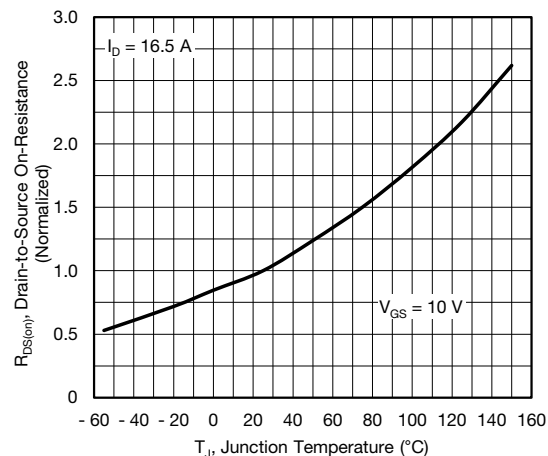
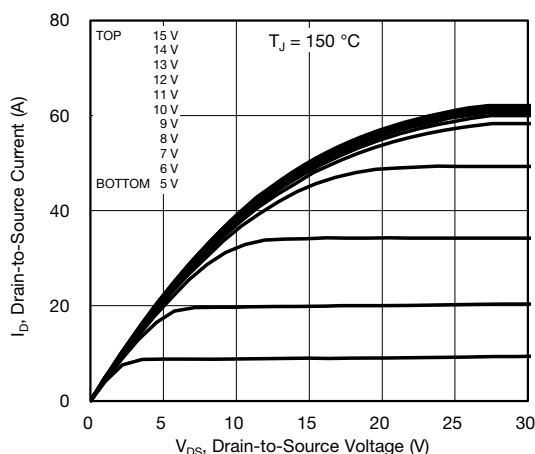
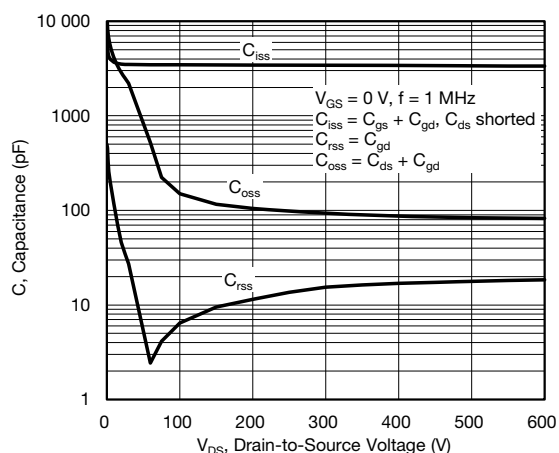
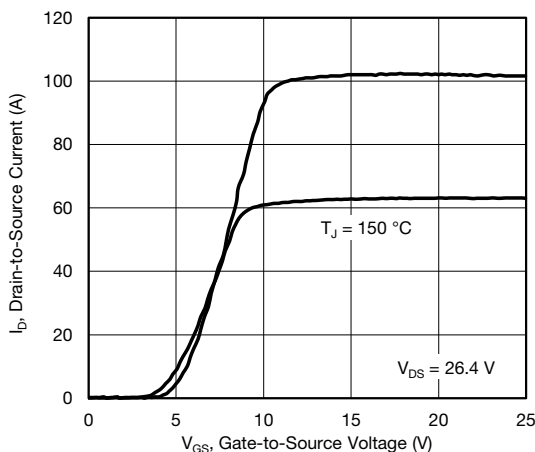
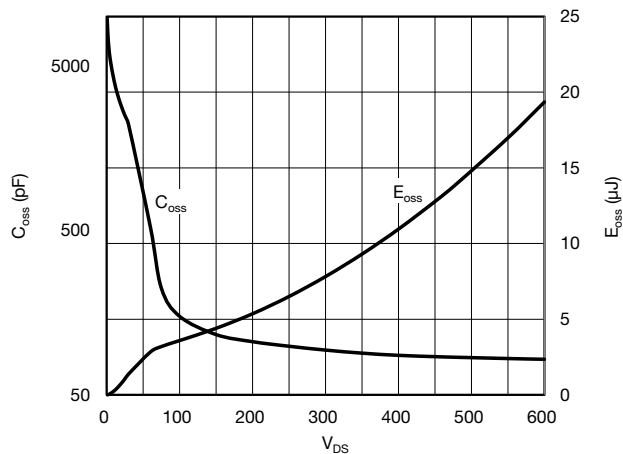
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.45	

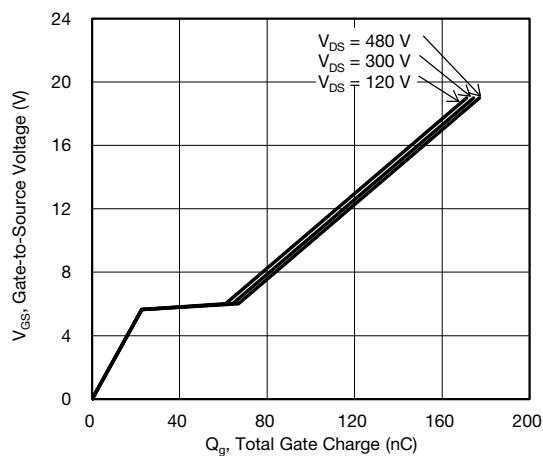
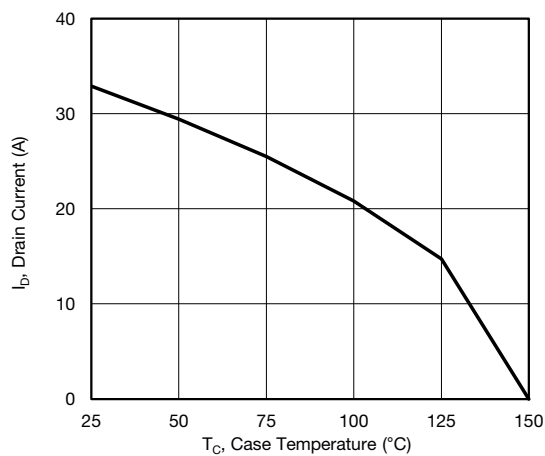
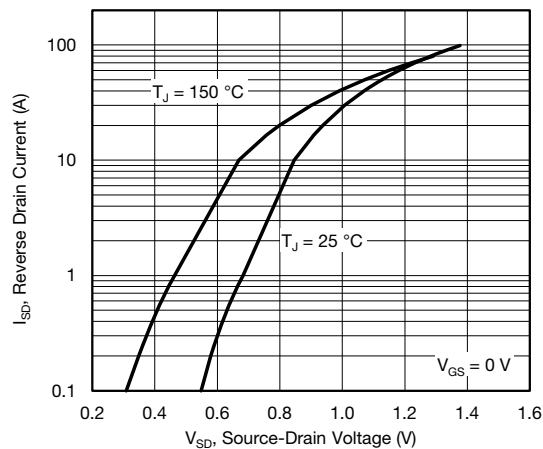
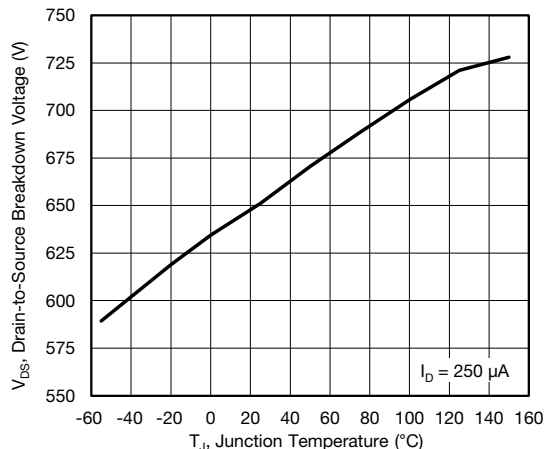
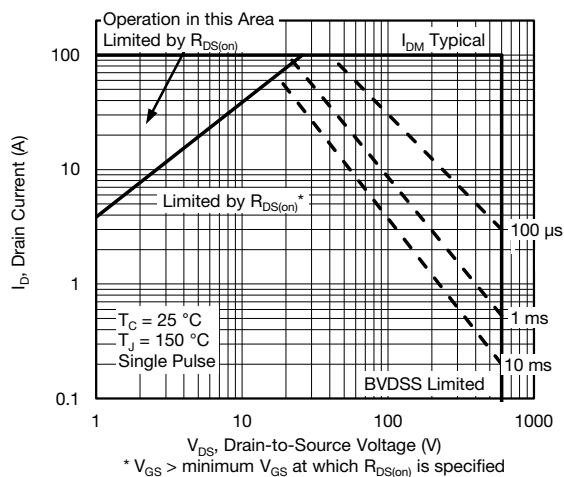
SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

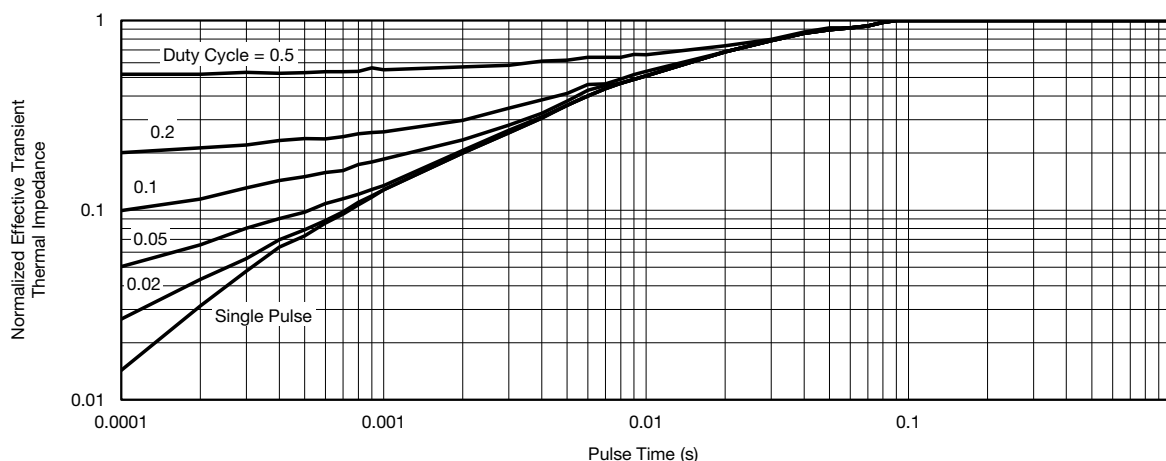
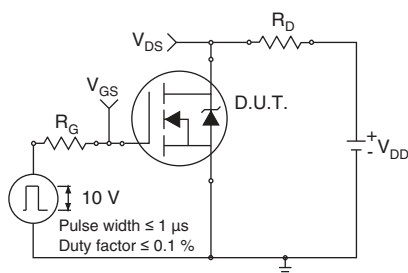
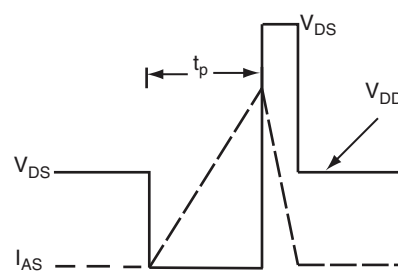
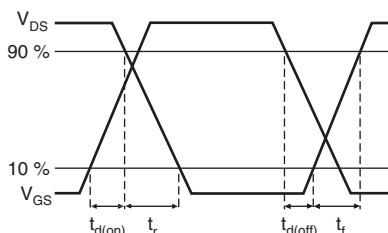
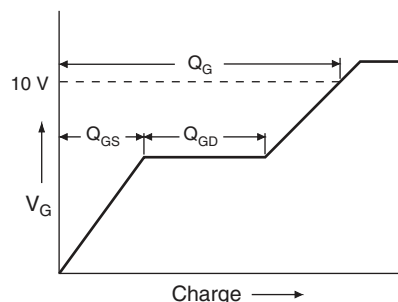
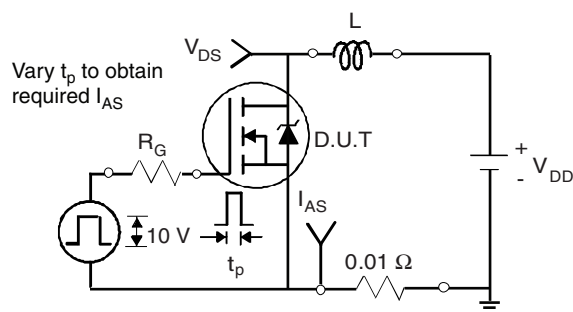
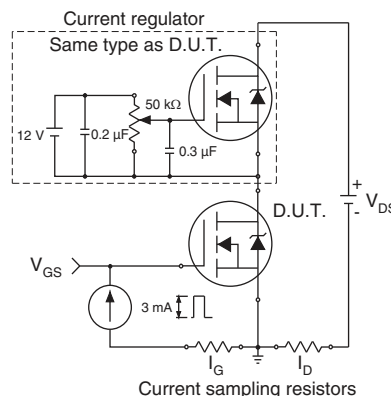
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		600	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA		-	0.72	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
		V _{GS} = ± 30 V		-	-	± 1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 480 V, V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 480 V, V _{GS} = 0 V, T _J = 125 °C		-	-	500	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 16.5 A	-	0.085	0.098	Ω
Forward Transconductance ^a	g _{fs}	V _{DS} = 30 V, I _D = 16.5 A		-	12	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz		-	3454	-	pF
Output Capacitance	C _{oss}			-	154	-	
Reverse Transfer Capacitance	C _{rss}			-	8	-	
Effective Output Capacitance, Energy Related ^b	C _{o(er)}	V _{GS} = 0 V, V _{DS} = 0 V to 480 V		-	121	-	
Effective Output Capacitance, Time Related ^c	C _{o(tr)}			-	437	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 16.5 A, V _{DS} = 480 V	-	103	155	nC
Gate-Source Charge	Q _{gs}			-	22	-	
Gate-Drain Charge	Q _{gd}			-	43	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 480 V, I _D = 16.5 A R _g = 9.1 Ω, V _{GS} = 10 V		-	28	56	ns
Rise Time	t _r			-	43	86	
Turn-Off Delay Time	t _{d(off)}			-	161	242	
Fall Time	t _f			-	48	96	
Gate Input Resistance	R _g	f = 1 MHz, open drain		-	0.5	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	33	A
Pulsed Diode Forward Current	I _{SM}			-	100	-	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 16.5 A, V _{GS} = 0 V		-	0.9	1.2	V
Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 16.5 A, dI/dt = 100 A/μs, V _R = 25 V		-	162	324	ns
Reverse Recovery Charge	Q _{rr}			-	1.0	2.0	μC
Reverse Recovery Current	I _{RRM}			-	13	-	A

Notes

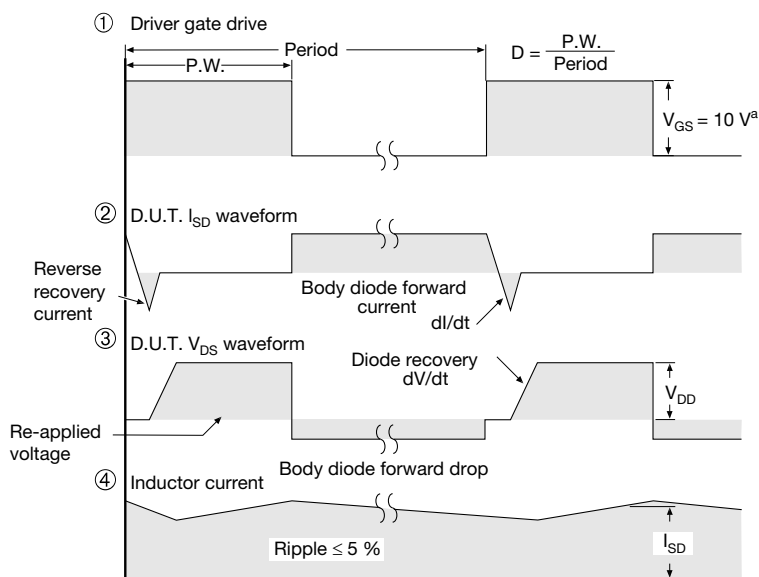
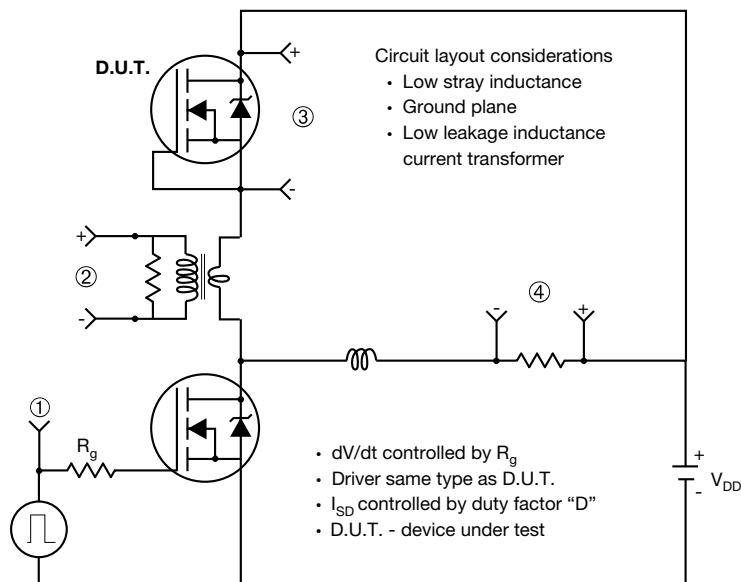
- a. Repetitive rating; pulse width limited by maximum junction temperature.
b. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .
c. $C_{oss(tr)}$ is a fixed capacitance that gives the charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 2 - Typical Output Characteristics

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 3 - Typical Transfer Characteristics

Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

Fig. 10 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Typical Source-Drain Diode Forward Voltage

Fig. 11 - Typical Drain-to-Source Voltage vs. Temperature

Fig. 9 - Maximum Safe Operating Area


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

Fig. 13 - Switching Time Test Circuit

Fig. 16 - Unclamped Inductive Waveforms

Fig. 14 - Switching Time Waveforms

Fig. 17 - Basic Gate Charge Waveform

Fig. 15 - Unclamped Inductive Test Circuit

Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



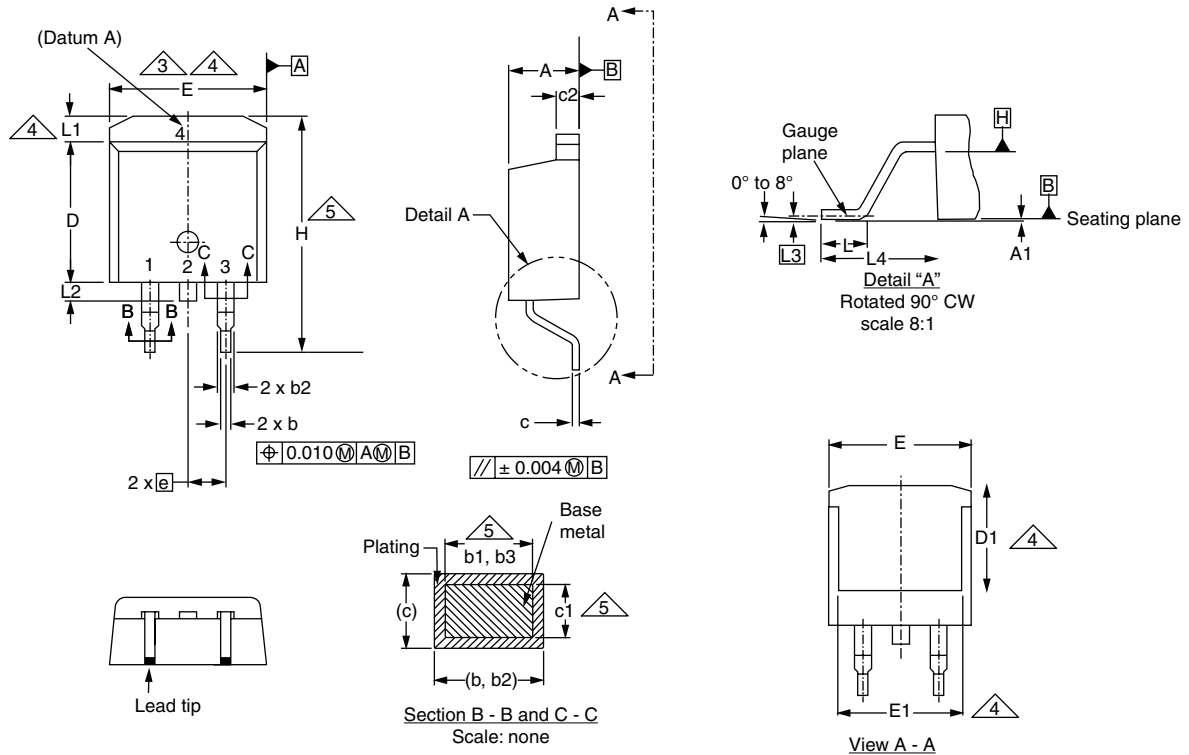
Note

a. $V_{GS} = 5 \text{ V}$ for logic level devices

Fig. 19 - For N-Channel

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TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

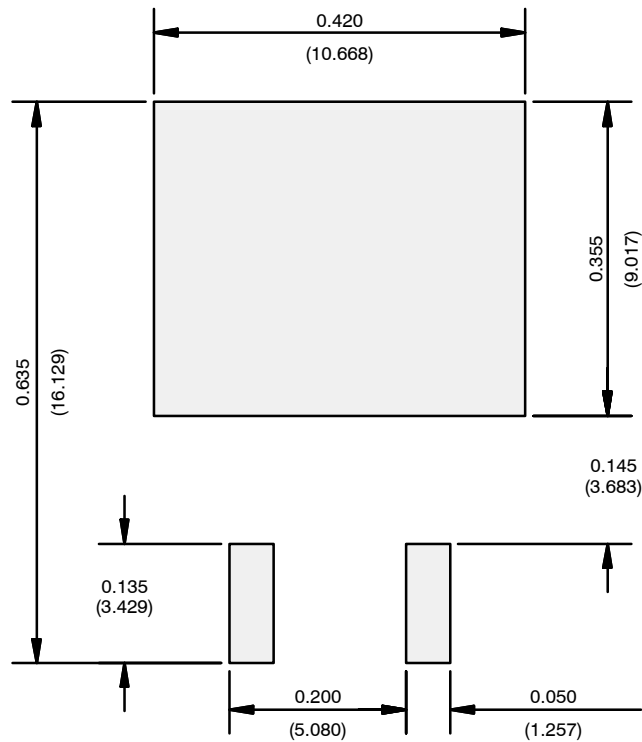
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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